

KP-3216P3C(1206)

IR LED Phototransistor

- Made with NPN silicon phototransistor chips.

FEATURES

- Mechanically and spectrally matched to the KP-3216 series infrared Emitting LED lamp
- Water clear lens
- Package: 2000pcs/ Reel
- Moisture sensitivity Level: Level 3
- RoHS compliant

ABSOLUTE MAXIMUM RATING $T_A=25^\circ\text{C}$

Parameter	Max. Ratings
Collector-to-Emitter Voltage	30V
Emitter-to-Collector Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	$-40^\circ\text{C} \sim +85^\circ\text{C}$
Storage Temperature Range	$-40^\circ\text{C} \sim +85^\circ\text{C}$

ELECTRICAL AND OPTICAL CHARACTERISTICS $T_A=25^\circ\text{C}$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
$V_{BR\ CE0}$	Collector-to-Emitter Breakdown Voltage	30	-	-	V	$I_C = 100\mu\text{A}$ $E_e = 0\text{mW}/\text{cm}^2$
$V_{BR\ EC0}$	Emitter-to-Collector Breakdown Voltage	5	-	-	V	$I_E = 100\mu\text{A}$ $E_e = 0\text{mW}/\text{cm}^2$
$V_{CE\ (SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	$I_C = 2\text{mA}$ $E_e = 20\text{mW}/\text{cm}^2$
I_{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE} = 10\text{V}$ $E_e = 0\text{mW}/\text{cm}^2$
T_R	Rise Time (10% to 90%)	-	15	-	μs	$V_{CE} = 5\text{V}$ $I_C = 1\text{mA}$
T_F	Fall Time (90% to 10%)	-	15	-	μs	$R_L = 1\text{K}\Omega$
$I\ (ON)$	On State Collector Current	0.1	0.3	-	mA	$V_{CE} = 5\text{V}$ $E_e = 1\text{mW}/\text{cm}^2$ $\lambda = 940\text{nm}$

DIMENSION

3.2mm x 1.6mm x 1.1mm(1206)

